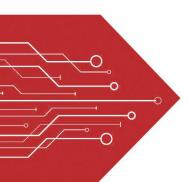
MSKSEMI















ESD

TVS

TSS

MOV

GDT

PLED

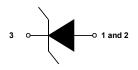
Broduct data sheet





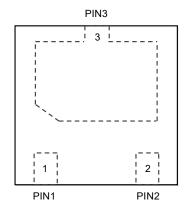


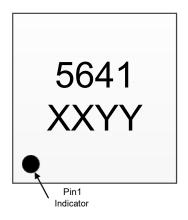




Circuit diagram

Pin configuration (Top View)





Marking

5641 = Series code XX = Device code

YY = Date code

Descriptions

The MSESD5641DXX-3 is a transient voltage suppressor designed to protect power interfaces. It is suitable to replace multiple discrete components in portable electronics.

The MSESD5641DXX-3 is specifically designed to protect USB port. TVS diode with higher surge capability is used to protect USB voltage bus pin.

The MSESD5641DXX-3 is available in DFN2×2-3L package. Standard products are Pb-free and Halogen-free.

Features

Reverse stand-off voltage: 7.5V ~15V

Surge protection according to IEC61000-4-5
 8/20µs waveform: I_{PPM} see Table 4
 Surge protection according to IEC61643-321
 10/1000µs waveform: I_{PPM} see Table 4

Low clamping voltage

Solid-state silicon technology

Applications

- Power supply protection
- Power management

Order information

Device	Package	Shipping	Device code
MSESD5641D07-3	DFN2×2-3L	3000/Tape&Reel	07
MSESD5641D10-3	DFN2×2-3L	3000/Tape&Reel	10
MSESD5641D12-3	DFN2×2-3L	3000/Tape&Reel	12
MSESD5641D15-3	DFN2×2-3L	3000/Tape&Reel	15

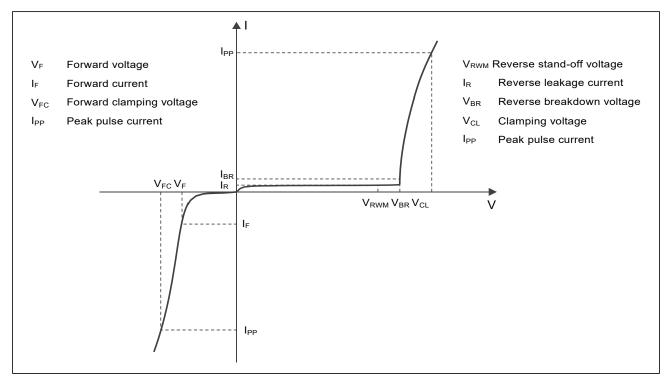


Parameter	Symbol	Rating	Unit	
Peak pulse power (tp=8/20µs) ¹⁾³⁾	P _{PK}	4000	W	
Peak pulse power (tp=10/1000µs) ²⁾³⁾	P _{PK}	350	W	
ESD according to IEC61000-4-2 air discharge	V	±30	kV	
ESD according to IEC61000-4-2 contact discharge	V _{ESD}	±30	ĸ۷	
Junction temperature	TJ	125	°C	
Operating temperature	T _{OP}	-40~85	°C	
Lead temperature	TL	260	°C	
Storage temperature	T _{STG}	-55~150	°C	

Notes:

- 1 Non-repetitive current pulse, according to IEC61000-4-5. (8/20µs current waveform)
- 2 Non-repetitive current pulse, according to IEC61643-321. (10/1000µs current waveform)
- 3 Measured from pin 3 to pin 1 and pin 2.

Electrical characteristics (T_A = 25°C, unless otherwise noted)



Definitions of electrical characteristics

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Electrical characteristics (T_A = 25°C, unless otherwise noted)

P/N	Reverse Standoff Voltage V _{RWM} (V)	Breakdown voltage V _{BR} (V) I _{BR} = 1mA		Reverse leakage current I _{RM} (nA) at V _{RWM}		Forward voltage V _F (V) I _F = 20mA		Junction capacitance F=1MHz, VR=0V (pF)		
	Max	Min	Тур	Max	Тур	Max	Min	Max	Тур	Max
MSESD5641D07-3	7.5	8.0	9.0	10.0	10	1000	0.45	1.25	2200	3000
MSESD5641D10-3	10.0	11.5	13.5	15.5	1	500	0.45	1.25	1500	2000
MSESD5641D12-3	12.0	13.0	15.0	17.0	1	100	0.45	1.25	1200	1800
MSESD5641D15-3	15.0	16.0	17.5	19.0	1	100	0.45	1.25	1000	1500

P/N	Rated peak pulse current I _{PP} (A) ¹⁾³⁾	Clamping voltage V _{CL} (V) at I _{PP} (A) ¹⁾³⁾	Rated peak pulse current lpp (A) ²⁾³⁾	Clamping voltage V _{CL} (V) at I _{PP} (A) ²⁾³⁾
	Max	Max	Max	Max
MSESD5641D07-3	190	18	28	13
MSESD5641D10-3	170	23	22	18
MSESD5641D12-3	150	27	16	20
MSESD5641D15-3	130	30	13	25

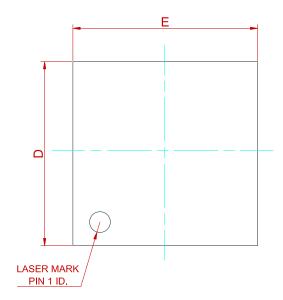
Notes:

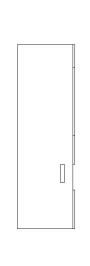
- 1) Non-repetitive current pulse, according to IEC61000-4-5. (8/20µs current waveform)
- 2) Non-repetitive current pulse, according to IEC61643-321. (10/1000µs current waveform)
- 3) Measured from pin 3 to pin 1 and pin 2.

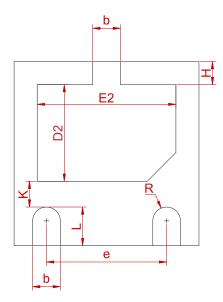


Compiance

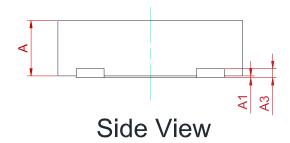
PACKAGE MECHANICAL DATA







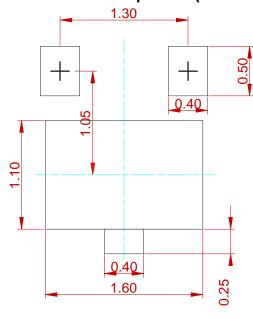
Top View



Bottom View

Cumbal	Dimensions In Millimeters			
Symbol	Min.	Тур.	Max.	
Α	0.50	0.58	0.65	
A1	0.00	0.02	0.05	
А3	0.10 REF.			
b	0.25	0.30	0.35	
D	1.90	2.00	2.10	
E	1.90	2.00	2.10	
D2	0.95	1.05	1.15	
E2	1.40	1.50	1.60	
е	1.20	1.30	1.40	
Н	0.20	0.25	0.30	
K	0.20	0.30	0.40	
L	0.33	0.39	0.45	
R	0.13	-	-	

Recommended land pattern (Unit: mm)



Notes:

This recommended land pattern is for reference purposes only. Please consult your manufacturing group to ensure your PCB design guidelines are met.

REEL SPECIFICATION

P/N	PKG	QTY
MSESD5641DXX-3	DFN2×2-3L	3000



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